



THE DATASHEET OF STGP3NB60HD





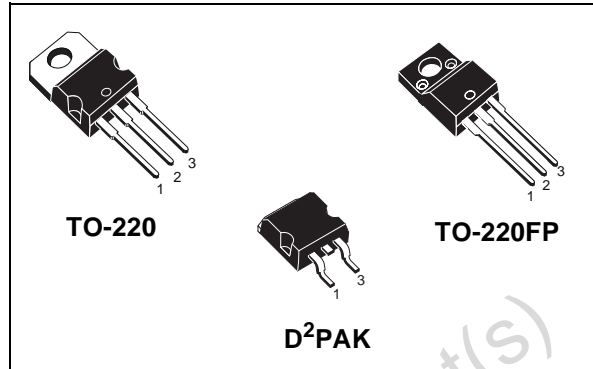
STGP3NB60HD - STGP3NB60HDFP STGB3NB60HD

N-CHANNEL 3A - 600V - TO-220/TO-220FP/D²PAK

PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)} (Max) @25°C	I _c (#) @100°C
STGB3NB60HD	600 V	< 2.8 V	6 A
STGP3NB60HD	600 V	< 2.8 V	6 A
STGP3NB60HDFP	600 V	< 2.8 V	6 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW GATE CHARGE
- HIGH FREQUENCY OPERATION
- HIGH CURRENT CAPABILITY
- OFF LOSSES INCLUDE TAIL CURRENT
- CO-PACKAGED WITH TURBOSWITCH™ ANTIPARALLEL DIODE



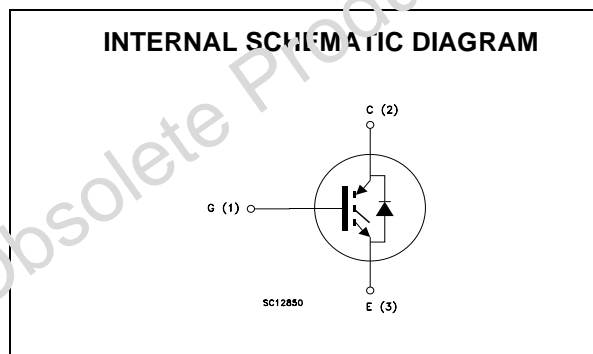
DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances.

The suffix "H" identifies a family optimized for high frequency applications (up to 50kHz) in order to achieve very high switching performances (reduced fall) maintaining a low voltage drop.

APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS and PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGB3NB60HDT4	GB3NB60HD	D ² PAK	TAPE & REEL
STGP3NB60HD	GP3NB60HD	TO-220	TUBE
STGP3NB60HDFP	GP3NB60HDFP	TO-220FP	TUBE

STGP3NB60HD - STGP3NB60HDFP - STGB3NB60HD

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STGP3NB60HD STGB3NB60HD	STGP3NB60HDFP	
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600		V
V _{GE}	Gate-Emitter Voltage	± 20		V
I _C	Collector Current (continuous) at T _C = 25°C (#)	10		A
I _C	Collector Current (continuous) at T _C = 100°C (#)	6		A
I _{CM} (■)	Collector Current (pulsed)	24		A
P _{TOT}	Total Dissipation at T _C = 25°C	50	25	W
	Derating Factor	0.4	0.2	W/°C
T _{stg}	Storage Temperature	-55 to 150		°C
T _j	Operating Junction Temperature			

(■) Pulse width limited by safe operating area

THERMAL DATA

		TO-220/D ² PAK	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case Max	2.5	5	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CES)}	Collector-Emitter Breakdown Voltage	I _C = 250 μA, V _{GE} = 0	600			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{CE} = Max Rating, T _C = 25 °C V _{CE} = Max Rating, T _C = 125 °C			50 100	μA μA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ±20V, V _{CE} = 0			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} , I _C = 250μA	3		5	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} = 15V, I _C = 3 A V _{GE} = 15V, I _C = 3 A, T _j = 125°C		2.4 1.9	2.8	V V

(#) Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

ELECTRICAL CHARACTERISTICS (CONTINUED)

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward Transconductance	$V_{CE} = 25\text{ V}, I_C = 3\text{ A}$		2.4		S
C_{ies} C_{oes} C_{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0$		235 33 6.6		pF pF pF
Q_g Q_{ge} Q_{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 480\text{ V}, I_C = 3\text{ A},$ $V_{GE} = 15\text{ V}$		21 6 7.6	27	nC nC nC
I_{CL}	Latching Current	$V_{clamp} = 480\text{ V}, T_j = 125^\circ\text{C}$ $R_G = 10\ \Omega$	12			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{CC} = 480\text{ V}, I_C = 3\text{ A}$ $R_G = 10\ \Omega, V_{GE} = 15\text{ V}$		5 11		ns ns
$(di/dt)_{on}$ Eon	Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 480\text{ V}, I_C = 3\text{ A}, R_G = 10\ \Omega$ $V_{GE} = 15\text{ V}, T_j = 125^\circ\text{C}$		400 77		A/ μs μJ

SWITCHING OFF

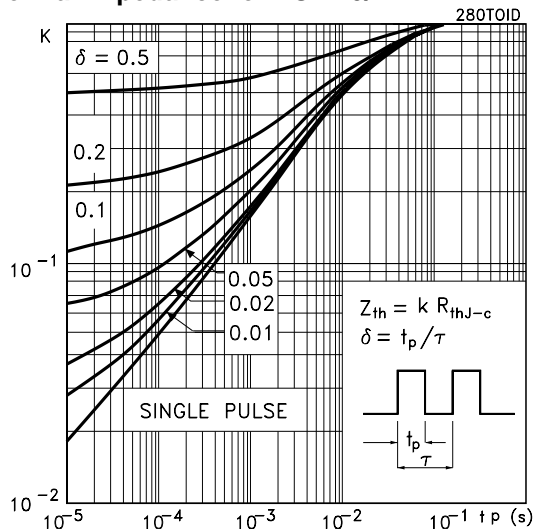
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c $t_r(V_{off})$ $t_{d(off)}$ t_f $E_{off(**)}$ E_{ts}	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 480\text{ V}, I_C = 3\text{ A},$ $R_{GE} = 10\ \Omega, V_{GE} = 15\text{ V}$		76 36 53 77 33 110		ns ns ns ns μJ μJ
t_c $t_r(V_{off})$ $t_{d(off)}$ t_f $E_{off(**)}$ E_{ts}	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 480\text{ V}, I_C = 3\text{ A},$ $R_{GE} = 10\ \Omega, V_{GE} = 15\text{ V}$ $T_j = 125^\circ\text{C}$		180 82 58 110 88 165		ns ns ns ns μJ μJ

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by max. junction temperature.
(**)Losses include Also the Tail (Jedec Standardization)

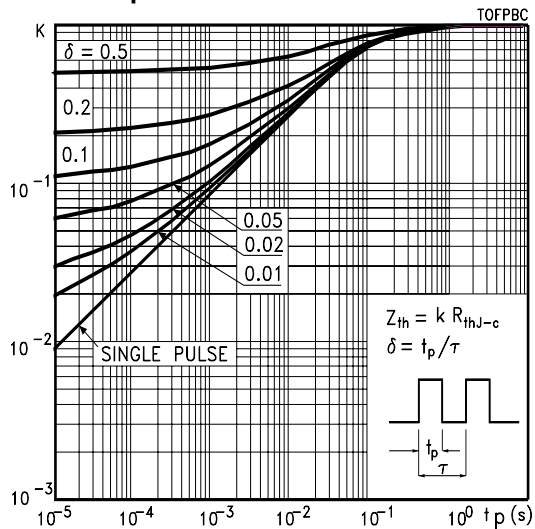
COLLECTOR-EMITTER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_f I_{fm}	Forward Current Forward Current pulsed				3 24	A A
V_f	Forward On-Voltage	$I_f = 3\text{ A}$ $I_f = 3\text{ A}, T_j = 125^\circ\text{C}$		1.6 1.4	2.0	V V
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 3\text{ A}, V_R = 35\text{ V},$ $T_j = 125^\circ\text{C}, di/dt = 100\text{ A}/\mu\text{s}$		45 70 2.7		ns nC A

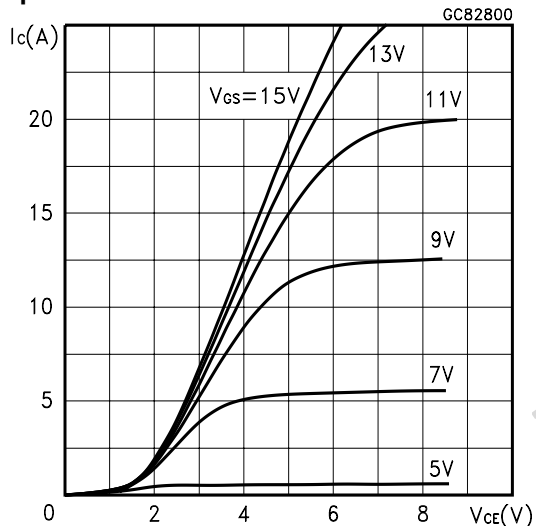
Thermal Impedance for TO-220/D²PAK



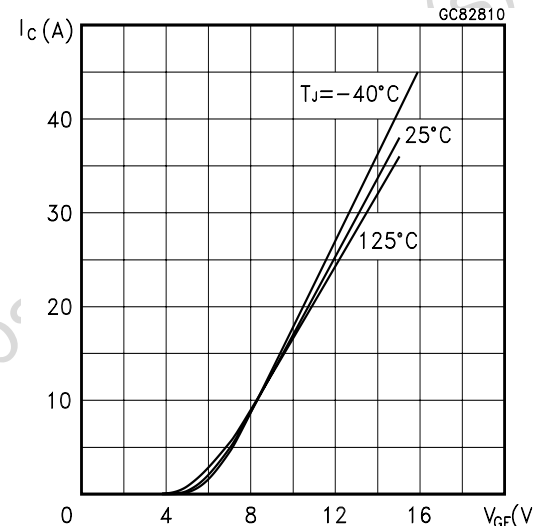
Thermal Impedance for TO-220FP



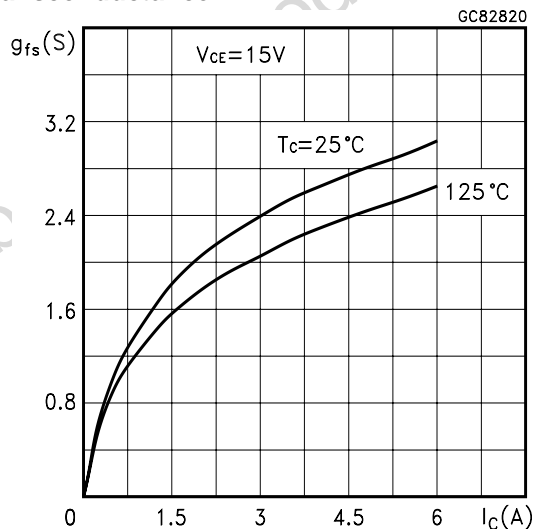
Output Characteristics



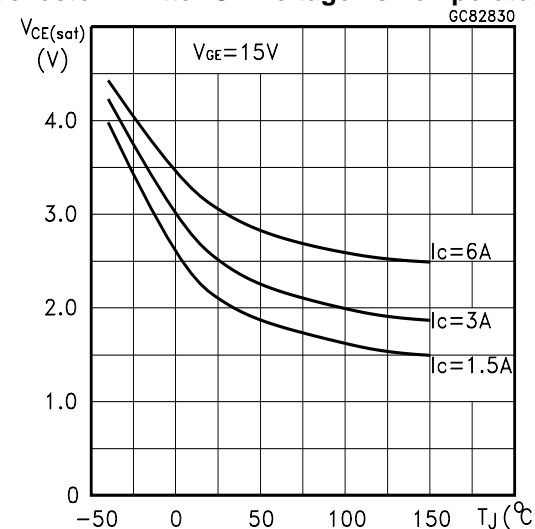
Transfer Characteristics



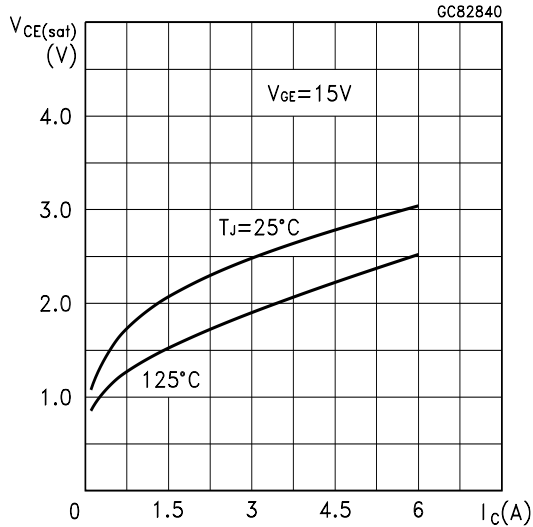
Transconductance



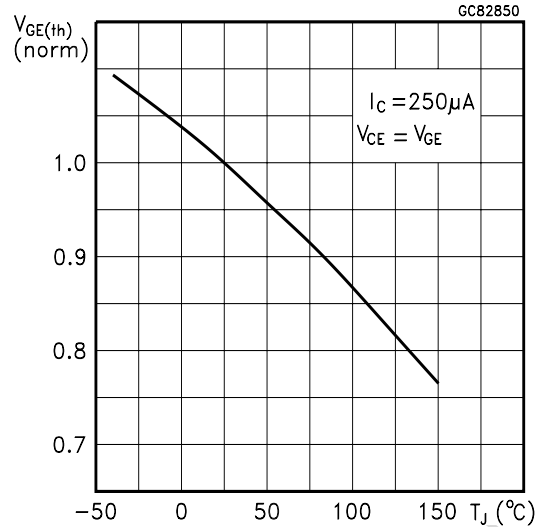
Collector-Emitter On Voltage vs Temperature



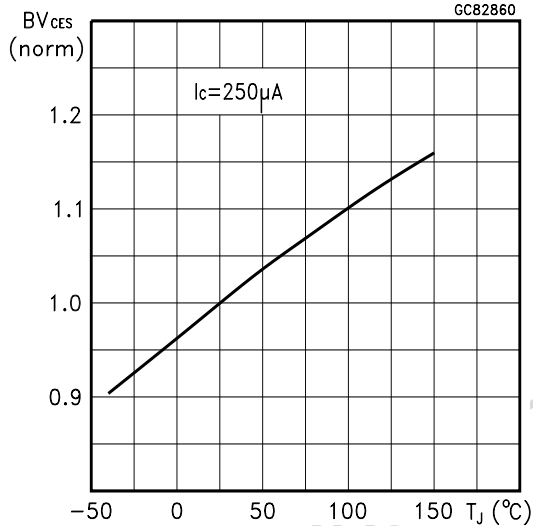
Collector-Emitter On Voltage vs Collector Current



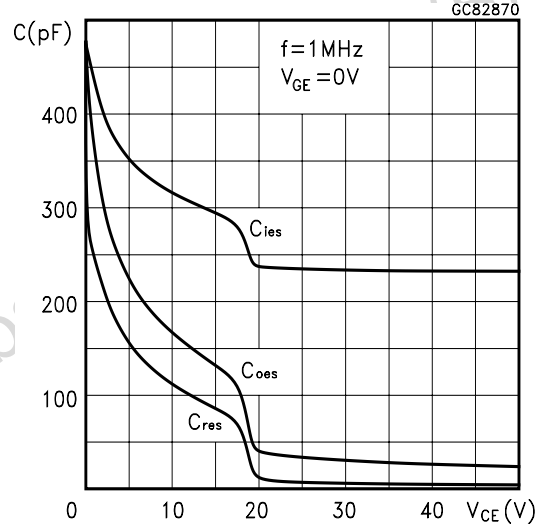
Gate Threshold vs Temperature



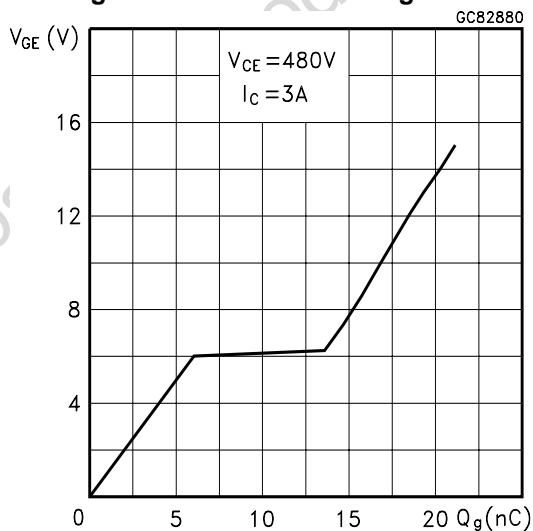
Normalized Breakdown Voltage vs Temperature



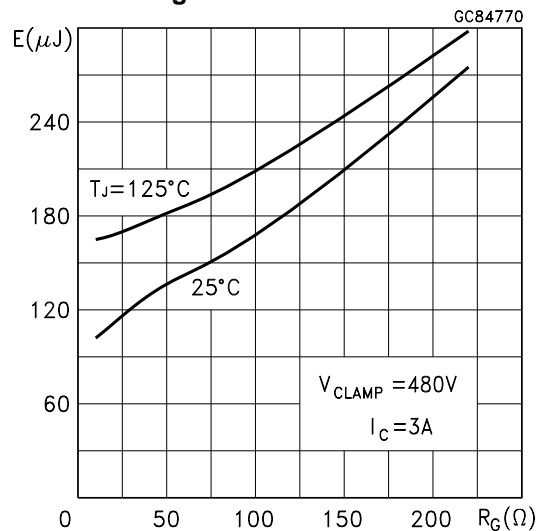
Capacitance Variations



Gate Charge vs Gate-Emitter Voltage

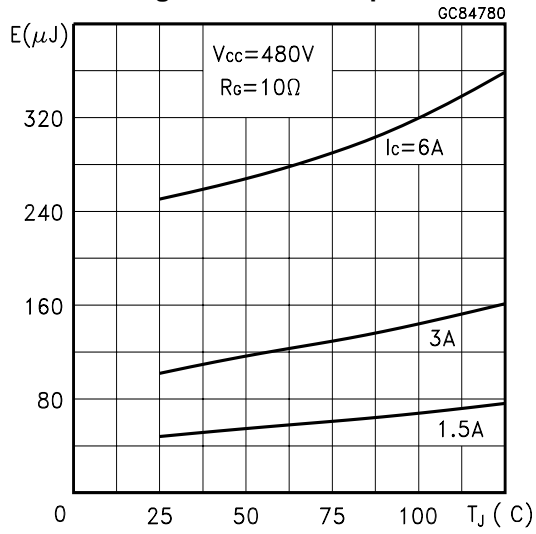


Total Switching Losses vs Gate Resistance

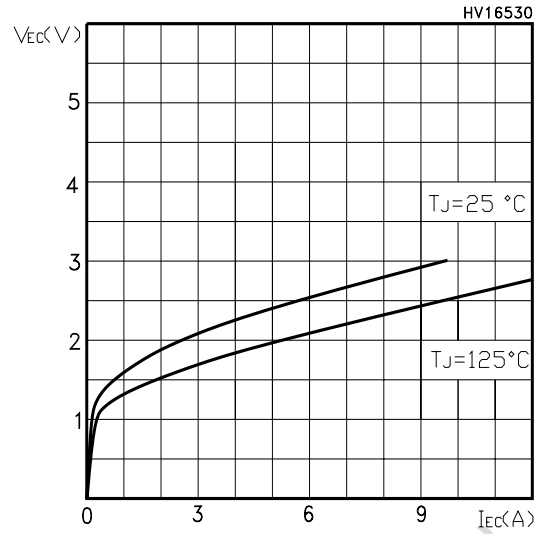


STGP3NB60HD - STGP3NB60HDFP - STGB3NB60HD

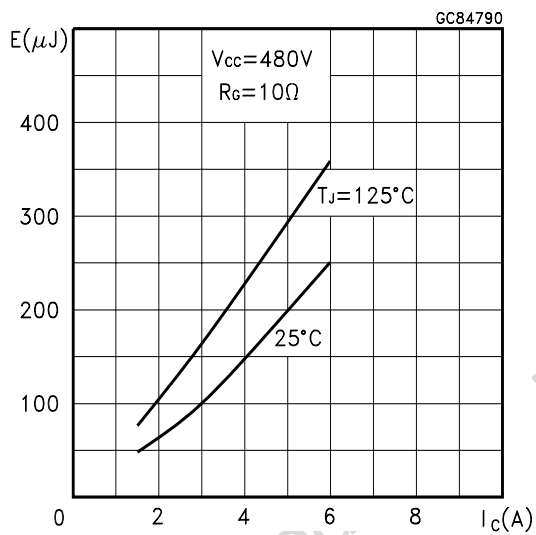
Total Switching Losses vs Temperature



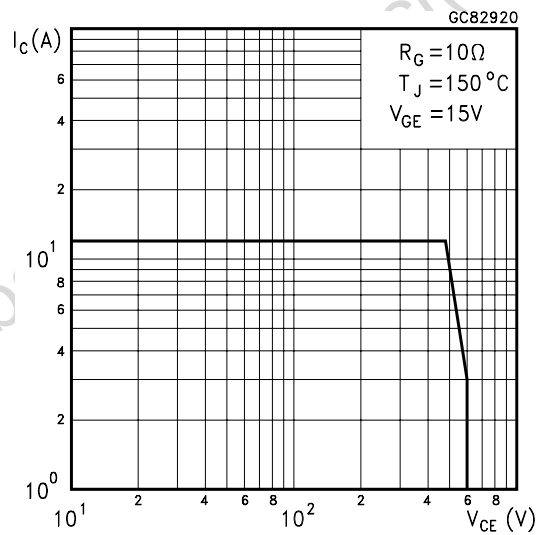
Emitter-collector Diode Characteristics



Total Switching Losses vs Collector Current



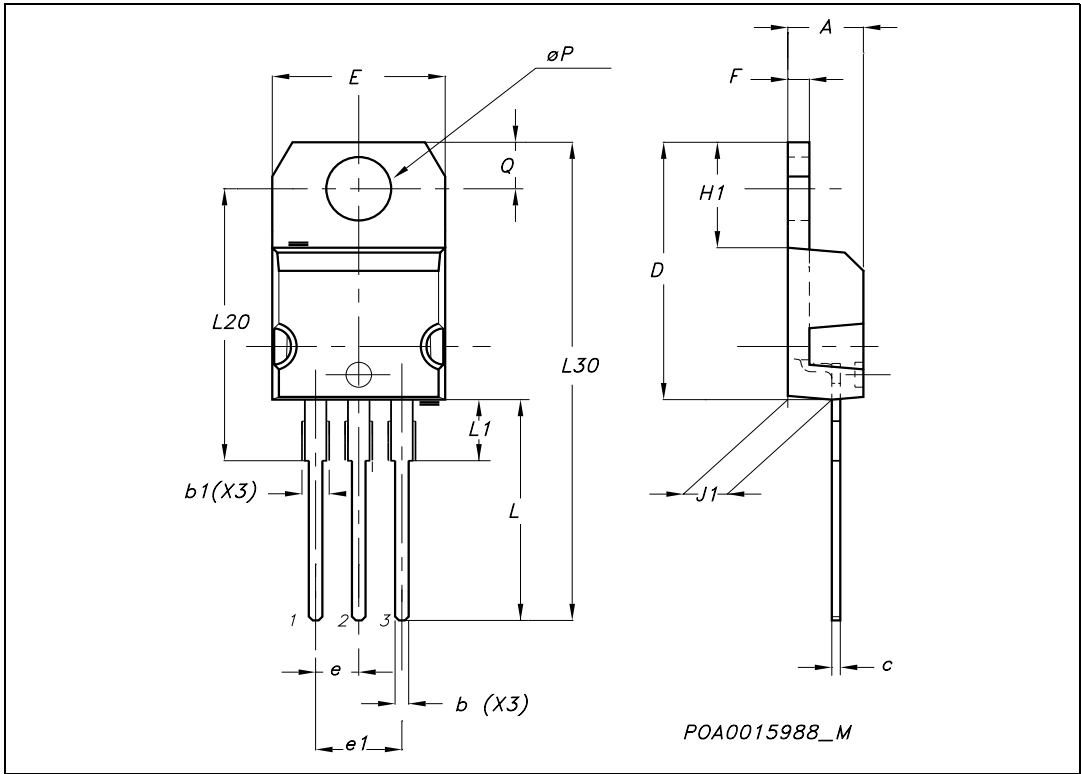
Switching Off Safe Operating Area



Obsolete Proc

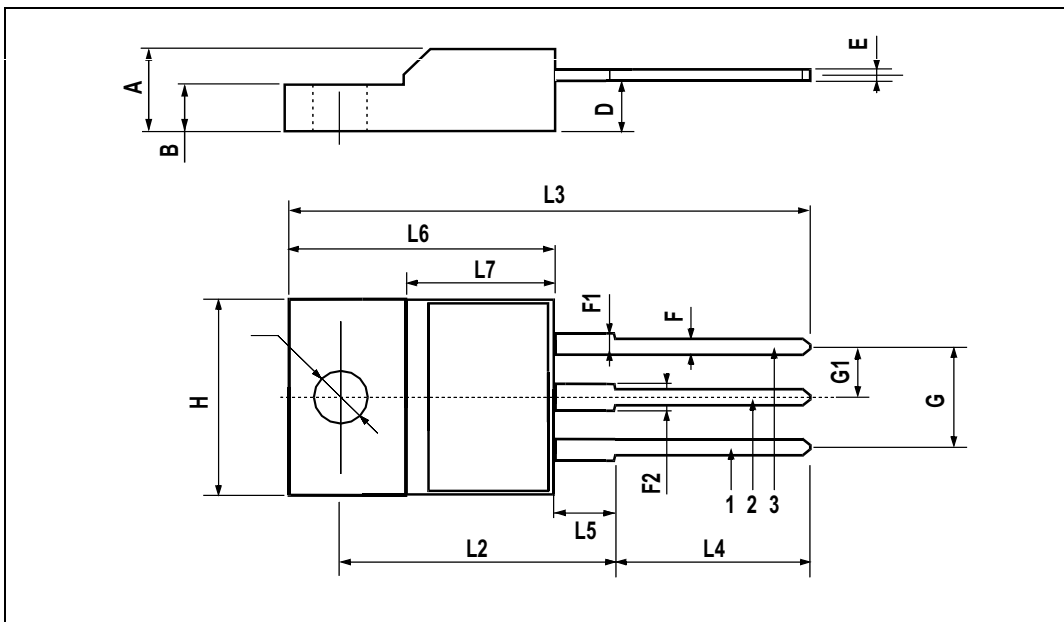
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



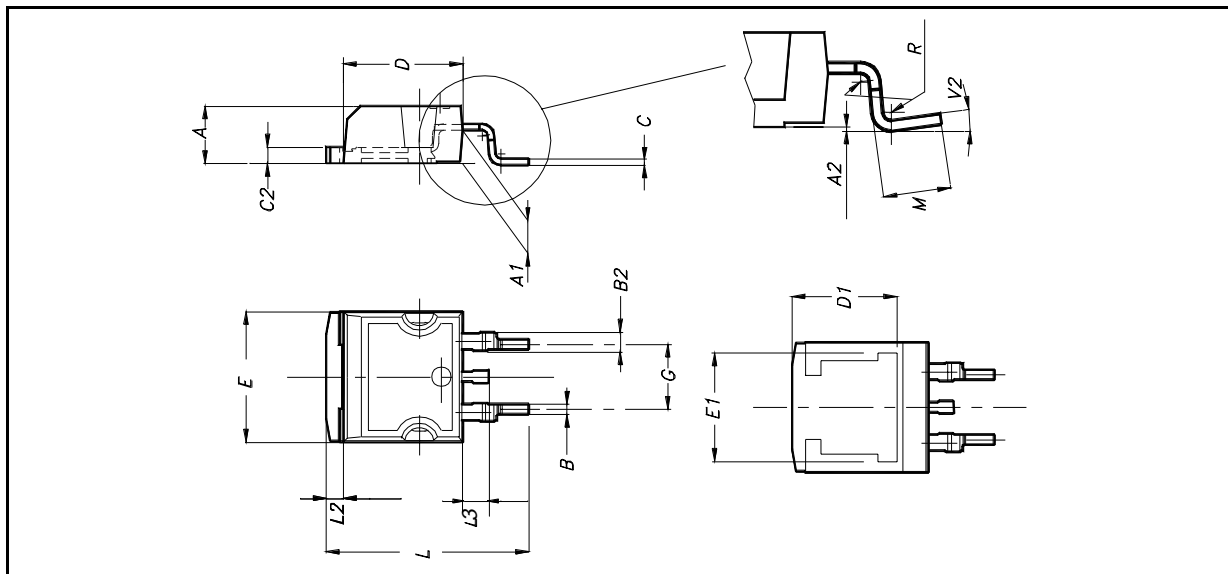
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



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